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Comment on "Epitaxial Pb(Zr,Ti)O$_3$ thin films with coexisting tetragonal and rhombohedral phases"

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In a recent paper, Oh and Jang (OJ)[1] reported on (001) PZT thin film, epitaxially grown on a (001) MgO substrate. It was shown that for compositions Zr/Ti=70/30 and Zr/Ti=80/20, x-ray diffraction patterns exhibit both tetragonal and rhombohedral features. Such compositions correspond to rhombohedral Zr-rich region of the T-x phase diagram of bulk PZT[2,3]. The authors explained the shift of morphotropic phase boundary (MPB) to Zr-side by the presence of stress caused by different ferro-/paraelectric as well as thermal expansion properties of the film and the substrate.

Here we present some corrections to the theory of this effect proposed by OJ. They assumed that spontaneous strain x_1 of the film-substrate system, under the condition $\lambda_{fc}(T^p - T) \ll 1$, can be expressed as [Eq. (4) of Ref. 1]

$$x_1 \approx (\lambda_{fc} - \lambda_s)(T^p - T), \tag{1}$$

where λ_{fc} and λ_s are thermal expansion coefficients of film and substrate, respectively, and T^p – the processing (annealing) temperature.

We consider stress (σ_i) related parts of the Gibbs function (ΔG) for both PZT film and MgO substrate. Following OJ, we assume that the film is thin enough so that the stress can be approximated by a spatially uniform average value. Additionally, we consider the near-boundary layer of the substrate, omitting the nonhomogenous terms in this case as well. For PZT thin film

$$\begin{aligned}\Delta G \;=\;& \lambda_{fc}(T^p - T)(\sigma_1 + \sigma_2 + \sigma_3)\\ &-\frac{1}{2}s_{11}(\sigma_1^2 + \sigma_2^2 + \sigma_3^2)\\ &-s_{12}(\sigma_1\sigma_2 + \sigma_2\sigma_3 + \sigma_1\sigma_3)\\ &-\frac{1}{2}s_{44}(\sigma_4^2 + \sigma_5^2 + \sigma_6^2)\\ &-Q_{11}(\sigma_1 P_1^2 + \sigma_2 P_2^2 + \sigma_3 P_3^2) - Q_{12}[\sigma_1(P_2^2 + P_3^2)\\ &+\sigma_2(P_1^2 + P_3^2) + \sigma_3(P_1^2 + P_2^2)]\\ &-Q_{44}(\sigma_4 P_2 P_3 + \sigma_5 P_1 P_2 + \sigma_6 P_1 P_3),\end{aligned} \tag{2}$$

where P_i are ferroelectric order parameter components. The rest of the notations are standard. We would like to emphasize that the first term in (2) is important since we are interested in the effects of the thermal expansion[4].

For the cubic paraelectric substrate (primed symbols):

$$\begin{aligned}\Delta G' \;=\;& \lambda_s(T^p - T)(\sigma'_1 + \sigma'_2 + \sigma'_3)\\ &-\frac{1}{2}s'_{11}({\sigma'_1}^2 + {\sigma'}_2^2 + {\sigma'}_3^2)\\ &-s'_{12}({\sigma'}_1\sigma'_2 + \sigma'_2\sigma'_3 + \sigma'_1\sigma'_3)\\ &-\frac{1}{2}s'_{44}({\sigma'}_4^2 + {\sigma'}_5^2 + {\sigma'}_6^2),\end{aligned} \tag{3}$$

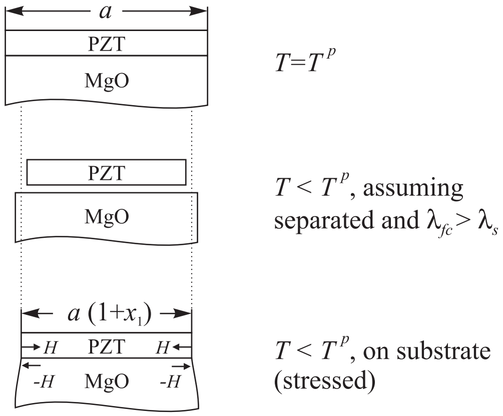
a
PZT
MgO
$T=T^p$
PZT
MgO
$T < T^p$, assuming separated and $\lambda_{fc} > \lambda_s$
$a\,(1+x_1)$
H
PZT
H
$-H$
MgO
$-H$
$T < T^p$, on substrate (stressed)

FIG. 1: Thermal expansion of PZT thin film and MgO substrate along [100] direction. T – temperature, a – film extent at the processing temperature T^p, x_1 and H are strain and stress for $T < T^p$.

If there is no external stress applied, the spontaneous values are $\sigma_3 = \sigma_4 = \sigma_5 = \sigma'_3 = \sigma'_4 = \sigma'_5 = 0$[4]. In contrast to Eq. (1) of OJ, σ_6 and σ'_6 in general do not vanish because shear strain in the lower symmetry structure of the film evolves upon cooling, resulting in the stress from the substrate.

On the other hand, in the tetragonal phase of PZT $\sigma_6 = \sigma'_6 = 0$ and $\sigma_1 = \sigma_2 = H$, $\sigma'_1 = \sigma'_2 = H'$.

It follows that spontaneous strain components are

$$\begin{aligned}x_1 \;=\;& -\left(\frac{\partial \Delta G}{\partial \sigma_1}\right)_{T,P_i} = \lambda_{fc}(T - T^p) + (s_{11} + s_{12})H\\ &+Q_{11}P_1^2 + Q_{12}(P_2^2 + P_3^2)\\ x'_1 \;=\;& -\left(\frac{\partial \Delta G'}{\partial \sigma'_1}\right)_{T} = \lambda_s(T - T^p) + (s'_{11} + s'_{12})H',\end{aligned} \tag{4}$$

where for tetragonal phase, polarized along [001] $P_1 = P_2 = 0, P_3 \neq 0$, for rhombohedral phase $P_1 = P_2 \neq 0, P_3 \neq 0$, and $P_1 \neq P_3$ if H is finite.

It is clear from Fig. 1, that at the interface between the film and the substrate the following boundary conditions are satisfied

$$x_1 = x_1', \qquad H = -H'. \tag{5}$$

Now, it is straightforward from Eqs. (4) and (5)

$$\begin{aligned} x_1 &= \frac{(s_{11}' + s_{12}')\lambda_{fc} + (s_{11} + s_{12})\lambda_s}{s_{11}' + s_{12}' + s_{11} + s_{12}}(T - T^p) \\ &\quad + \frac{s_{11}' + s_{12}'}{s_{11}' + s_{12}' + s_{11} + s_{12}}[Q_{11}P_1^2 + Q_{12}(P_2^2 + P_3^2)], \\ H &= \frac{(\lambda_{fc} - \lambda_s)(T^p - T)}{s_{11}' + s_{12}' + s_{11} + s_{12}} \\ &\quad - \frac{Q_{11}P_1^2 + Q_{12}(P_2^2 + P_3^2)}{s_{11}' + s_{12}' + s_{11} + s_{12}}. \end{aligned} \tag{6}$$

As we mentioned above, in rhombohedral phase the spontaneous values $\sigma_6 \neq 0$ and $\sigma_6' \neq 0$, but they should be defined self-consistently form Eqs. (2), (3), and boundary conditions similar to those in (5)

$$\begin{aligned} x_6 = x_6' &= \frac{s_{44}'Q_{44}P_1P_3}{s_{44}' + s_{44}} \\ \sigma_6 = -\sigma_6' &= -\frac{Q_{44}P_1P_3}{s_{44}' + s_{44}} \end{aligned} \tag{7}$$

In summary, our approach does not require more than solving linear equations, if only terms of up to second order in stress are taken into account in ΔG and $\Delta G'$. At the same time, elastic properties of the substrate have to be taken into account to describe the film-substrate system thermal expansion, and the corrections to Eq. (1) appear even in the lowest order approximation.

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